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oxide/silicon nitride/silicon oxide/silicon nitride, is deposited over the patterned third metallic layer 30 and the silicon oxide layer 40, and

- openings are created through the optical interference layer 60 and the silicon-oxide insulation layer 40, these openings expose the surfaces of bond pad 20 and interconnections (not shown) created on the surface of the first layer 41 of metal.

IN THE CLAIMS

A19

1. (Amended) A method of forming insulating material alignment posts associated with active device structures comprising:
providing a silicon semiconductor wafer having patterned said active device therein and thereon; and
forming said insulating material alignment posts in a pattern over said pattern of active device structures, said insulating material alignment posts comprising an optical interference multilayer stack in addition to comprising an optical interference layer.

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8. (Amended) A method of forming a device structure that combines insulating materials for alignments posts and optical interference layers associated with an active device structure in a silicon body comprising:

providing a silicon wafer having a pattern of active device structures therein and thereon;

forming a first metallic layer over the surface of said wafer;

forming a second metallic layer over the said silicon oxide, which is used both for connections and for bonding pads;

forming a silicon dioxide insulation over the said second metal layer;

forming a third metallic layer over the surface of said layer of silicon dioxide;

forming a photoresist mask over the said third metallic layer having a covering over the planned pixel locations of the said liquid-crystal-on-silicon display device;

removing the said third metallic layer not covered by the said photoresist mask;

removing the said photoresist mask to provide that each said pixel retains said metallic layer, which shall act as a mirror reflector for the light incident upon said liquid-crystal-on-silicon display device; and

depositing optical interference layers of silicon oxide/silicon nitride/silicon oxide/silicon nitride over said third metallic layer and said silicon dioxide layer.

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22. (Amended) The method of claim 17 for etch-back removal of said silicon nitride, except that silicon nitride deposited in the said post cavities.

33. Please cancel claim 33.

34. Please cancel claim 3.

35. Please cancel claim 35.

36. Please cancel claim 36.

IN THE DRAWINGS

The drawings have been amended to correct errors and omissions, a copy of the updated drawings is attached.

Examiner J. Vockrodt is thanked for his thorough examination of the Prior Art, he is also thanked for his indication of allowing claims 8-21 and 23-32.

Claims 33-36 have been cancelled.